

BYC20-600

Rectifier diode, hyperfast

Rev. 01 — 28 November 2007

Product data sheet

1. Product profile

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features

- Extremely fast switching
- Reduces switching loss in associated MOSFET
- Low thermal resistance
- Low reverse recovery current

1.3 Applications

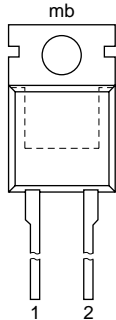

- Half-bridge or full-bridge switched-mode power supplies
- Half-bridge lighting ballasts
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \leq 600$ V
- $V_F = 1.54$ V (typ)
- $I_{F(AV)} \leq 20$ A
- $t_{rr} = 19$ ns (typ)

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		 001aaa020
2	anode (a)		
mb	mounting base; cathode		

SOD59 (2-lead TO-220AC)

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BYC20-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; $\delta = 1.0$; $T_{mb} \leq 100\text{ °C}$	-	500	V
$I_{F(AV)}$	average forward current	square waveform; $\delta = 0.5$; $T_{mb} \leq 93\text{ °C}$	-	20	A
I_{FRM}	repetitive peak forward current	square waveform; $\delta = 0.5$; $T_{mb} \leq 93\text{ °C}$; $t_p = 25\text{ }\mu\text{s}$;	-	40	A
I_{FSM}	non-repetitive peak forward current	$t = 10\text{ ms}$; sinusoidal waveform	-	250	A
		$t = 8.3\text{ ms}$; sinusoidal waveform	-	274	A
T_{stg}	storage temperature		-40	+150	°C
T_j	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; see Figure 1	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

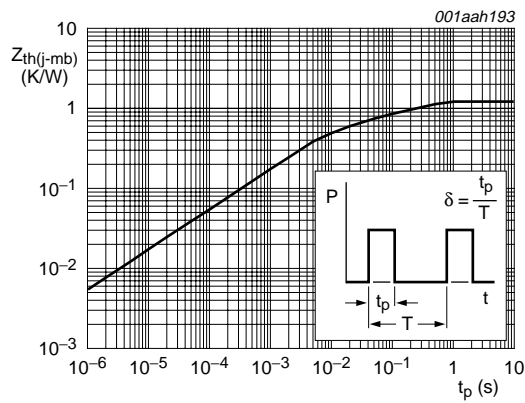


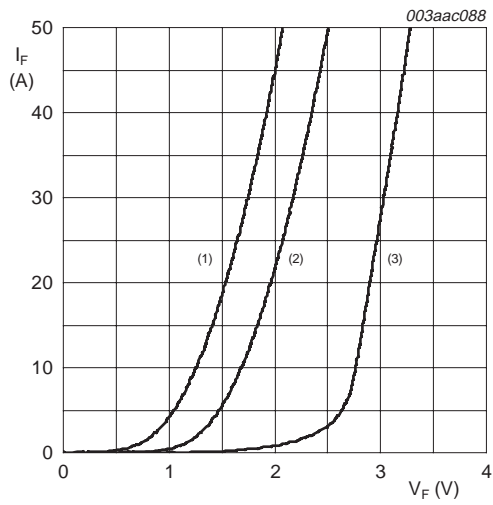
Fig 1. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 5. Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 20\text{ A}$; $T_j = 150\text{ °C}$; see Figure 2	-	1.54	1.97	V
		$I_F = 40\text{ A}$; $T_j = 150\text{ °C}$; see Figure 2	-	1.95	2.34	V
		$I_F = 20\text{ A}$; see Figure 2	-	1.89	2.9	V
I_R	reverse current	$V_R = 600\text{ V}$	-	16	200	μA
		$V_R = 500\text{ V}$; $T_j = 100\text{ °C}$	-	1.6	3.0	mA
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$ to $V_R = 30\text{ V}$; $dI_F/dt = 50\text{ A}/\mu\text{s}$; see Figure 3	-	35	55	ns
		$I_F = 20\text{ A}$ to $V_R = 400\text{ V}$; $dI_F/dt = 500\text{ A}/\mu\text{s}$; see Figure 3	-			
		$T_j = 25\text{ °C}$	-	19	-	ns
		$T_j = 100\text{ °C}$	-	32	40	ns
I_{RM}	peak reverse recovery current	$I_F = 20\text{ A}$ to $V_R = 400\text{ V}$; $T_j = 125\text{ °C}$; see Figure 3	-			
		$dI_F/dt = 50\text{ A}/\mu\text{s}$	-	3.0	7.5	A
		$dI_F/dt = 500\text{ A}/\mu\text{s}$	-	9.5	12	A
V_{FR}	forward recovery voltage	$I_F = 20\text{ A}$; $dI_F/dt = 100\text{ A}/\mu\text{s}$; see Figure 4	-	8	11	V



- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values
- (2) $T_j = 150\text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values

Fig 2. Forward current as a function of forward voltage

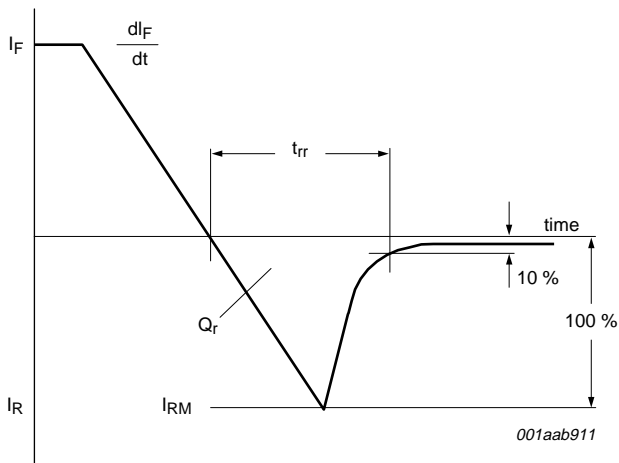


Fig 3. Reverse recovery definitions

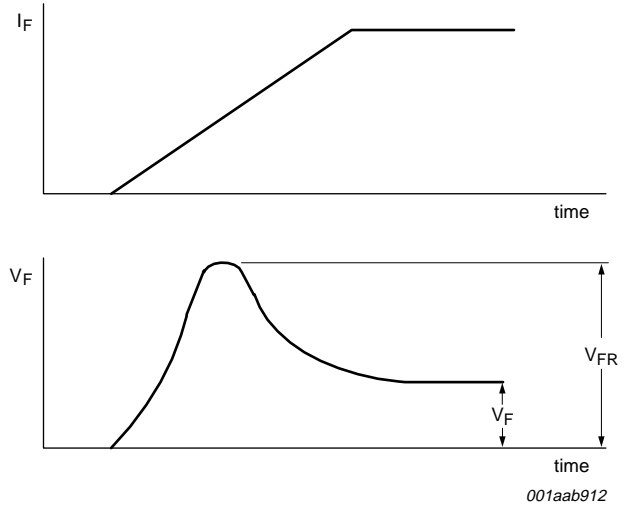
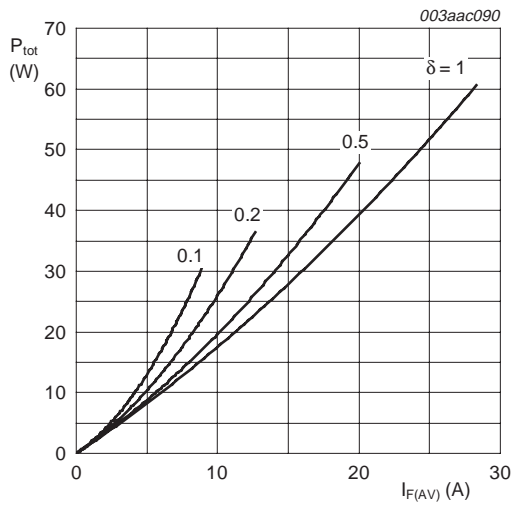
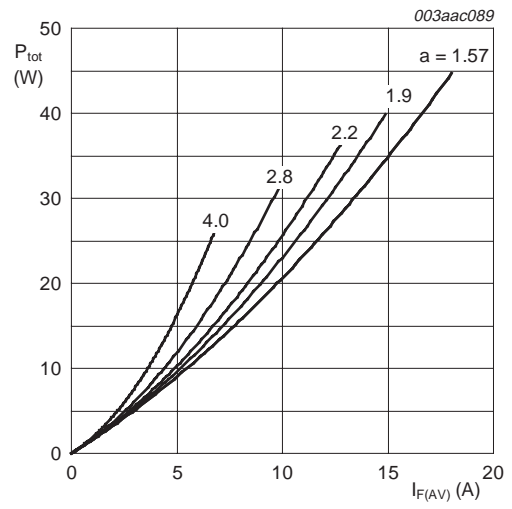


Fig 4. Forward recovery definitions



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59

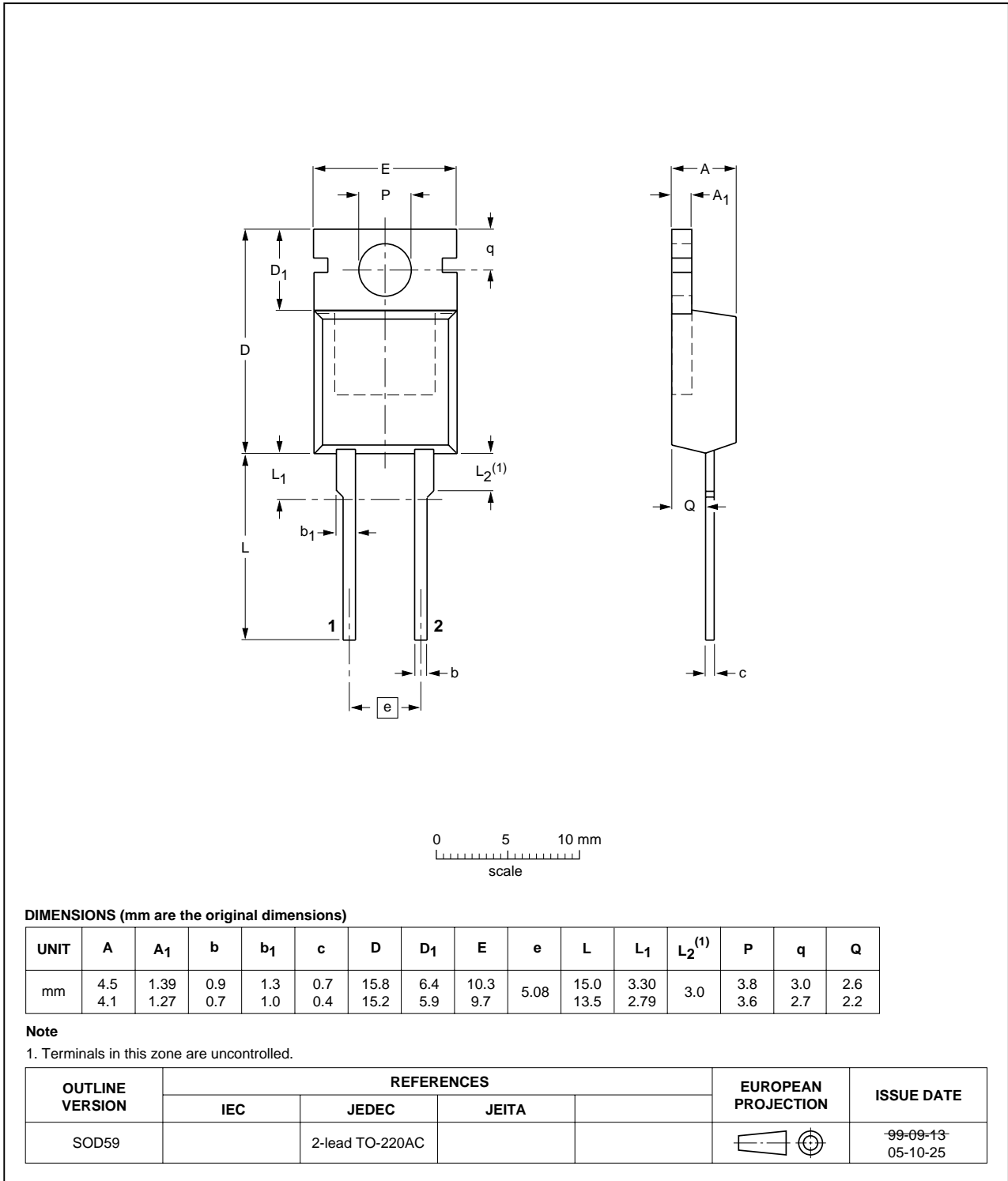


Fig 7. Package outline SOD59 (2-lead TO-220AC)

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC20-600_1	20071128	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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